



FIG.1

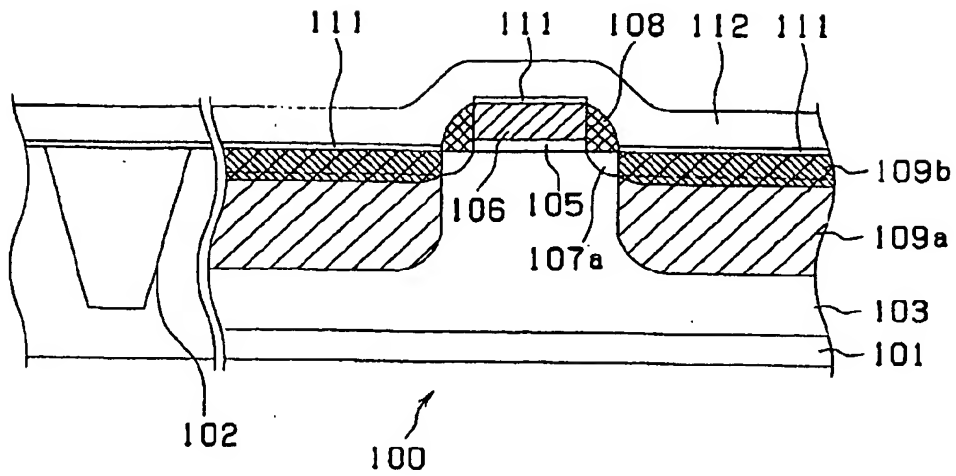


FIG.2

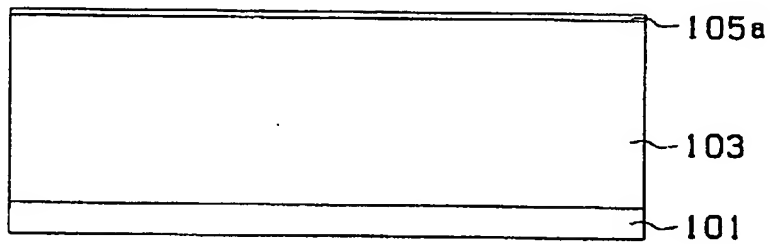
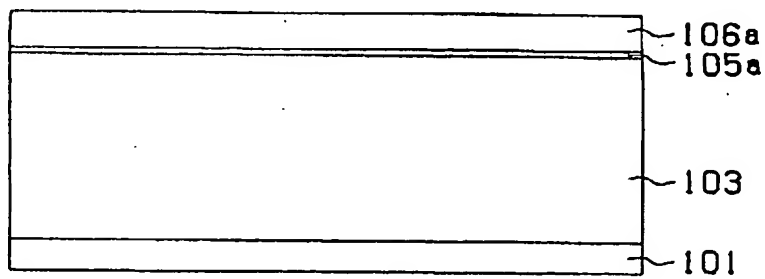


FIG.3



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FIG.4

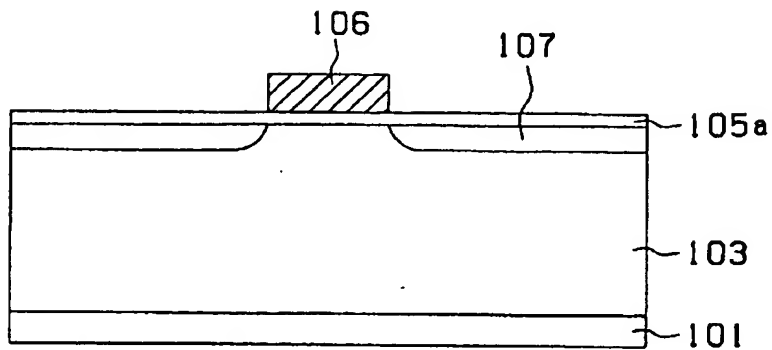


FIG.5

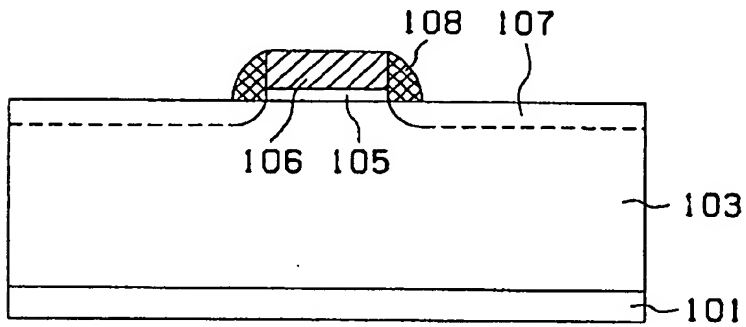
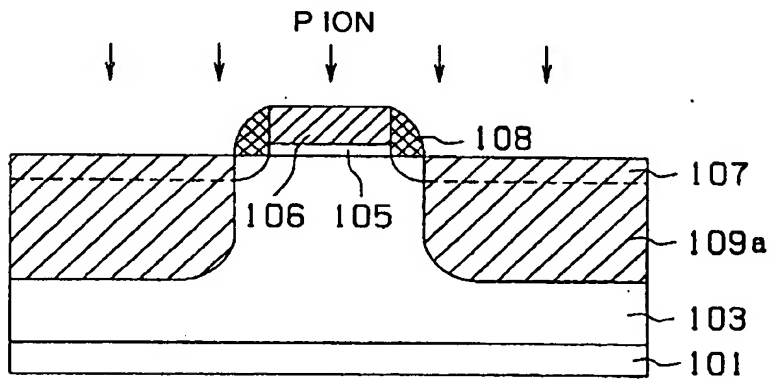


FIG.6



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FIG.7

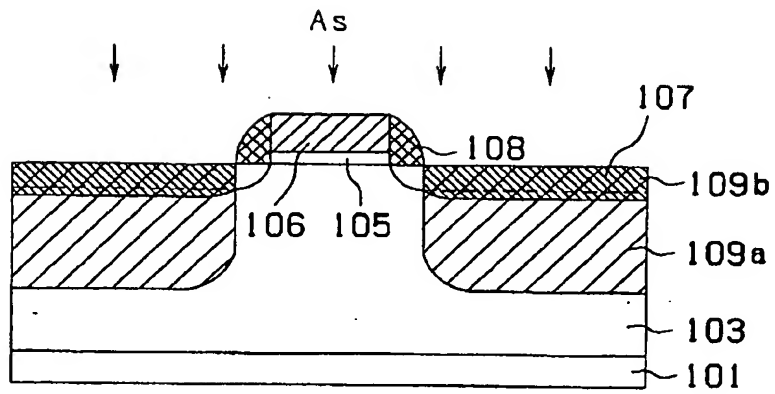
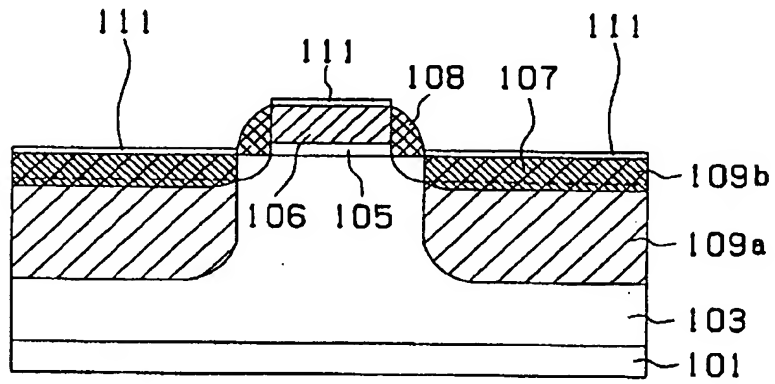


FIG.8



[illegible]

A cross-sectional view of a semiconductor device. A substrate 105 is shown with a thin layer 106 on its top surface. A curved surface 107a is formed on the substrate, with a cross-hatched region 108 at its top. A vertical line 109b is drawn through the center of the curved surface, and a curved line 109a is shown below it. Two vertical dimensions are indicated: R1, the distance from the horizontal line x1 to the top of the curved surface, and R2, the distance from the horizontal line x2 to the top of the curved surface. The horizontal line x2 is dashed, and the horizontal line x1 is solid.

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FIG.11

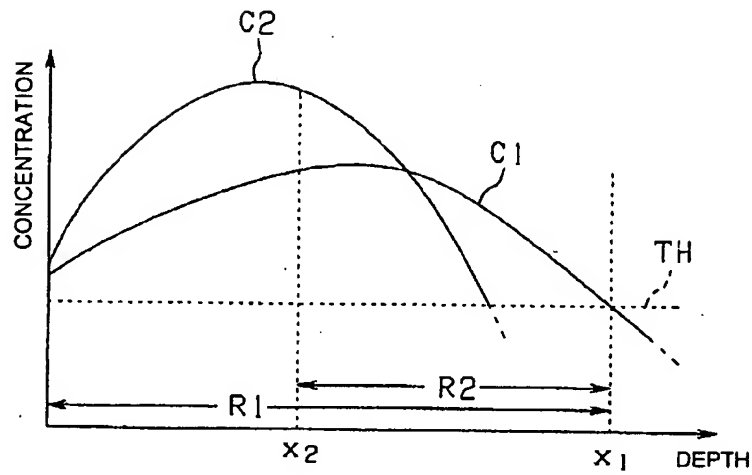
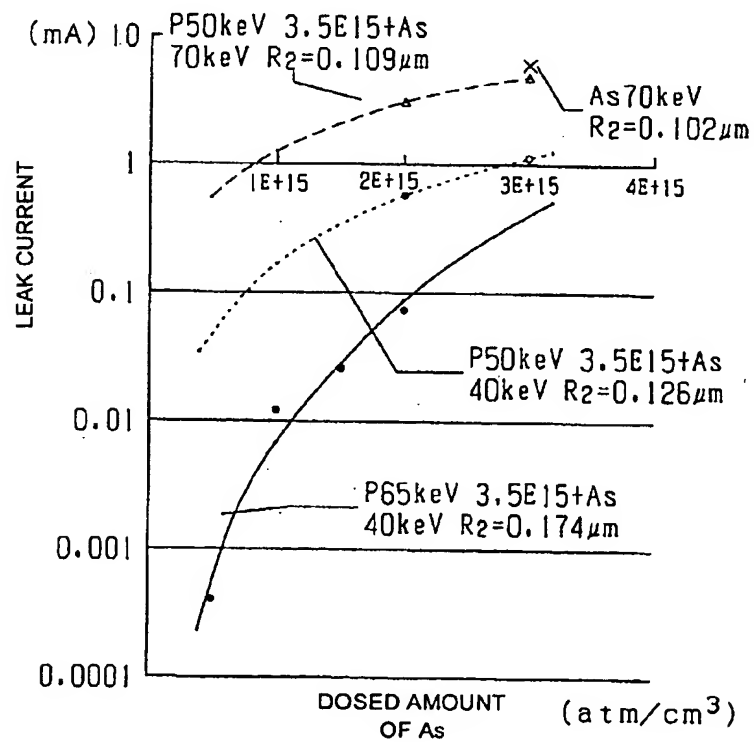


FIG.12



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FIG.13A

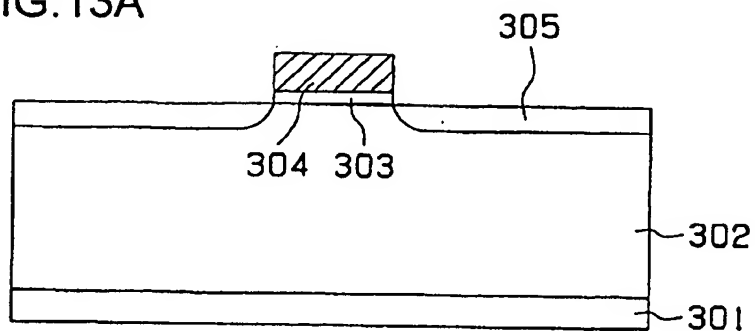


FIG.13B

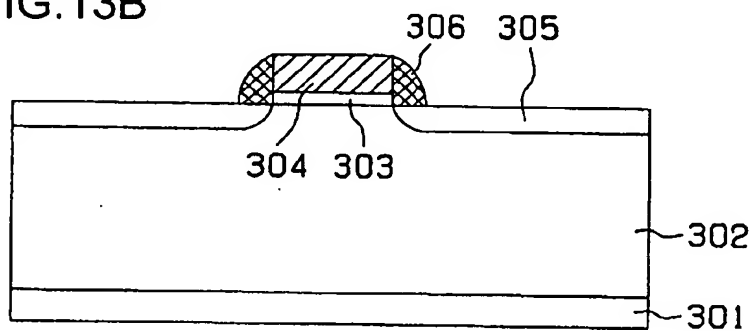


FIG.13C

